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8/19/02

Docket No.: M4065.0319/P319-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Ronald A. Weimer, et al.

Application No.: 09/912,558

Group Art Unit: 2813

Filed: July 26, 2001

Examiner: Erik J. Kielin

For: FABRICATION OF DRAM AND OTHER
SEMICONDUCTOR DEVICES WITH AN
INSULATING FILM USING A WET
RAPID THERMAL OXIDATION PROCESS

July
9/5/02

AMENDMENT UNDER 37 CFR §1.116

ATTN: BOX AF
Commissioner for Patents
Washington, DC 20231

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TECHNOLOGY CENTER 2800

Dear Sir:

This paper is in response to the Office Action dated May 8, 2002 finally rejecting claims 13, 14, 16, 17, 41, and 42, please amend the above-captioned U.S. Patent application as follows:

In the Claims:

Please replace claims 13 and 42 with amended claims 13 and 42 below.

13. (Three times amended) A method of fabricating a semiconductor device,
the method comprising:

depositing a dielectric film over an active region of a semiconductor substrate to
form part of a gate of a transistor; and

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Clerk 8/20/02